



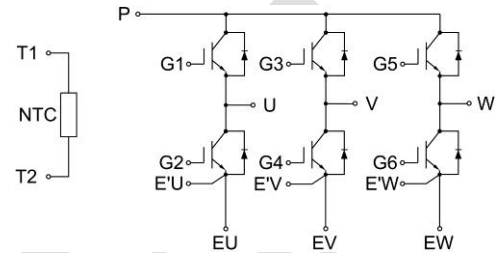
GT40FF120B3H

IGBT Module

Features:

- Trench & Field Stop IGBT
- Short Circuit Rated >10 μ s
- Low Saturation Voltage
- Low Switching Loss
- 100% RBSOA Tested(2xIc)
- Low Stray Inductance
- Lead Free, Compliant with RoHS Requirement

Circuit Diagram



Applications:

- Motor Drives
- Air Conditioning
- Servo Drives
- UPS

IGBT, Inverter Maximum Rated Values

V_{CES}	Collector-Emitter Blocking Voltage	$T_J=25^{\circ}C$	1200	V
V_{GES}	Gate-Emitter Voltage		± 20	V
I_C	Continuous Collector Current	$T_C=100^{\circ}C$	40	A
		$T_C=25^{\circ}C$	80	A
I_{CM}	Peak Collector Current Repetitive	$t_p=1ms$	80	A
t_{sc}	Short Circuit Withstand Time		>10	μs
P_D	Maximum Power Dissipation (IGBT)	$T_C=25^{\circ}C$ $T_{Jmax}=175^{\circ}C$	360	W



Electrical Characteristics of IGBT

Static Characteristics

Symbol	Description	Conditions	Min.	Typ.	Max.	Units
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=1mA, V_{CE}=V_{GE}, T_J=25^{\circ}C$	5.0	5.8	6.5	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=40A, V_{GE}=15V$	$T_J=25^{\circ}C$	1.80	2.10	V
			$T_J=125^{\circ}C$	2.10		
			$T_J=150^{\circ}C$	2.20		
I_{CES}	Collector-Emitter Leakage Current	$V_{GE}=0V, V_{CE}=V_{CES}, T_J=25^{\circ}C$			1	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=\pm 20V, V_{CE}=0V, T_J=25^{\circ}C$			200	nA
C_{ies}	Input Capacitance	$V_{CE}=25V, V_{GE}=0V, f=100kHz, T_J=25^{\circ}C$		3.44		nF
C_{oes}	Output Capacitance			0.51		
C_{res}	Reverse Transfer Capacitance			0.32		

Switching Characteristics

$t_{d(on)}$	Turn-on Delay Time	$V_{CC}=600V, I_C=40A, R_{Gon}=15\Omega, V_{GE}=\pm 15V, \text{Inductive Load}$	$T_J=25^{\circ}C$	92		ns
			$T_J=125^{\circ}C$	93		
			$T_J=150^{\circ}C$	94		
t_r	Rise Time		$T_J=25^{\circ}C$	46		ns
			$T_J=125^{\circ}C$	50		
			$T_J=150^{\circ}C$	50		
$t_{d(off)}$	Turn-off Delay Time		$T_J=25^{\circ}C$	183		ns
			$T_J=125^{\circ}C$	185		
			$T_J=150^{\circ}C$	189		
t_f	Fall Time	$T_J=25^{\circ}C$	258		ns	
		$T_J=125^{\circ}C$	310			
		$T_J=150^{\circ}C$	315			
E_{on}	Turn-on Switching Loss	$T_J=25^{\circ}C$	2.48		mJ	
		$T_J=125^{\circ}C$	2.68			
		$T_J=150^{\circ}C$	3.05			



E _{off}	Turn-off Switching Loss	V _{CC} =600V, I _C =40A, R _{Goff} =15Ω, V _{GE} =±15V, du/dt=2880V/μs(T _J =150°C), Inductive Load	T _J =25°C	3.21	mJ
			T _J =125°C	3.77	
			T _J =150°C	3.97	
Q _g	Total Gate Charge	V _{GE} =-15V...+15V	T _J =25°C	457	nC
RBSOA	I _C =80A, V _{CC} =1050V, V _P =1200V, R _G =15Ω, V _{GE} =+15V to 0V, T _J =150°C			Trapezoid	
I _{SC}	V _{CC} =600V, V _{GE} = ±15V, t _p =10us, R _{Gon} =56Ω, R _{Goff} =56Ω, T _J =25°C			175	A
R _{θJC}	IGBT Thermal Resistance: Junction-to-Case			0.417	°C/W

Diode, Inverter

Maximum Rated Values (T_C=25°C unless otherwise specified)

V _{RRM}	Repetitive Peak Reverse Voltage	T _J =25°C	1200	V
I _F	Diode Continuous Forward Current		40	A
I _{FM}	Peak FWD Current Repetitive	t _p =1ms	80	A

Electrical Characteristics of FWD (T_C=25°C unless otherwise specified)

Symbol	Description	Conditions	Min.	Typ.	Max.	Units
V _{FM}	Forward Voltage	I _F =40A	T _J =25°C	1.80	2.10	V
			T _J =125°C	1.90		
			T _J =150°C	1.90		
I _{rr}	Peak Reverse Recovery Current		T _J =25°C	53.7		A
			T _J =125°C	62.5		
			T _J =150°C	63.8		
t _{rr}	Reverse Recovery Time	I _F =40A, di/dt=830A/μs(T _J =150°C), V _{rr} =600V, V _{GE} =-15V	T _J =25°C	164		ns
			T _J =125°C	186		
			T _J =150°C	186		
Q _{rr}	Reverse Recovery Charge		T _J =25°C	4.53		μC
			T _J =125°C	6.31		
			T _J =150°C	6.54		



E _{rec}	Reverse Recovery Energy	I _F =40A, di/dt=830A/μs(T _J =150°C), V _{rr} =600V, V _{GE} =-15V	T _J =25°C	1.56	mJ
			T _J =125°C	2.14	
			T _J =150°C	2.45	
R _{θJC}	Diode Thermal Resistance: Junction-to-Case			0.584	°C/W

Internal NTC-Thermistor Characteristics

Symbol	Description		Min.	Typ.	Max.	Units.
R ₂₅	Rated Resistance	T _C =25°C		5		kΩ
ΔR/R	Deviation of R100	T _C =100°C, R ₁₀₀ =481Ω	-5		5	%
P ₂₅	Power Dissipation	T _C =25°C			10	mW
B _{25/50}	B-Value	$R_2=R_{25} \exp[B_{25/50}(1/T_2-1/(298.15K))]$		3380		K
B _{25/80}	B-Value	$R_2=R_{25} \exp[B_{25/80}(1/T_2-1/(298.15K))]$		3440		K



Module

Symbol	Description	Min.	Typ.	Max.	Units	
V _{ios}	Isolation Voltage (All Terminals Shorted)	AC Test Voltage, t=30s	4500		V	
Internal Isolation		Al ₂ O ₃				
d _{creep}	Creepage Distance: Terminal to Heatsink		11.5		mm	
	Creepage Distance: Terminal to Terminal		6.3			
d _{clear}	Clearance: Terminal to Heatsink		10.0		mm	
	Clearance: Terminal to Terminal		5.0			
L _{SCE}	Stray Inductance Module		25		nH	
T _J	Maximum Junction Temperature			175	°C	
T _{JOP}	Maximum Operating Junction Temperature Range	-40		+150	°C	
T _{stg}	Storage Temperature	-40		+125	°C	
CTI	Comparative Tracking Index	200				
R _{θCS}	Case-to-Sink Thermally (Conductive Grease Applied)			0.08	°C/W	
M	Mounting Torque for solder pins Module Mounting	Screw M4--Mounting according to valid application note	1.5		1.8	N·m
	Mounting Torque for press-fit pins Module Mounting	Screw M4--Mounting according to valid application note	1.0		1.5	N·m
G	Weight		23		g	

Ordering Information Table

Device code	G	T	40	FF	120	B3	H
	①	②	③	④	⑤	⑥	⑦

- ① - IGBT Module
- ② - Trench, Low Switching Losses IGBT
- ③ - Rated Current (40=40A)
- ④ - Circuit Configuration (FF=Full Bridge)
- ⑤ - Rated Voltage (120=1200V)
- ⑥ - Package Type
- ⑦ - Test Level (Pass the Important Reliability Test-Industrial Grade)

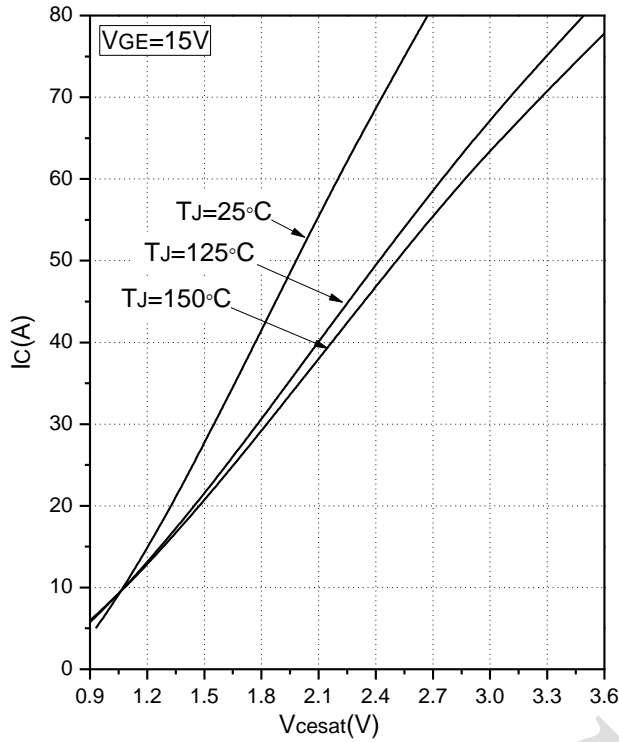


Fig.1 Typical Saturation Voltage Characteristics

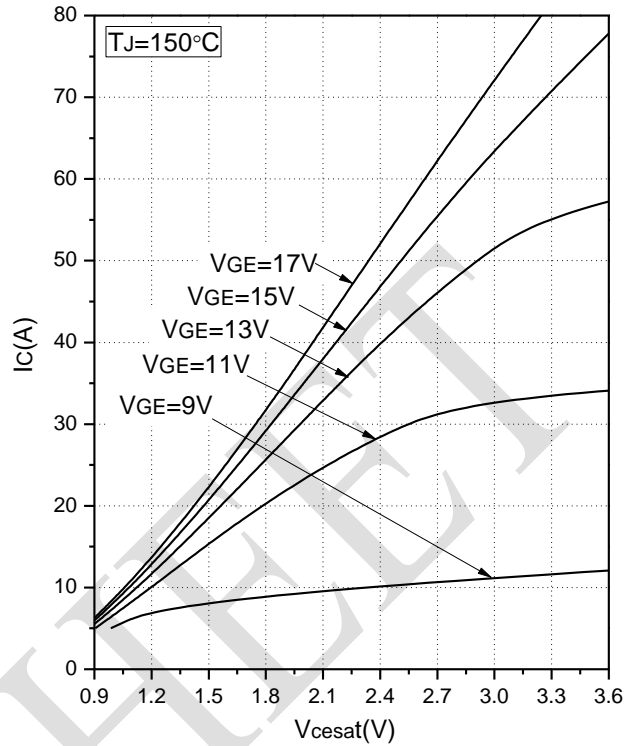


Fig.2 Typical Output Characteristics

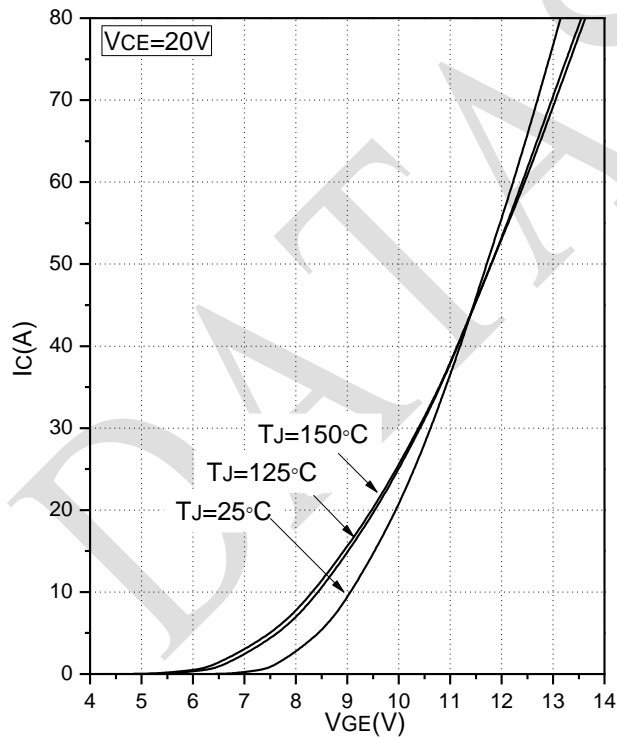


Fig.3 Forward Characteristics of FWD

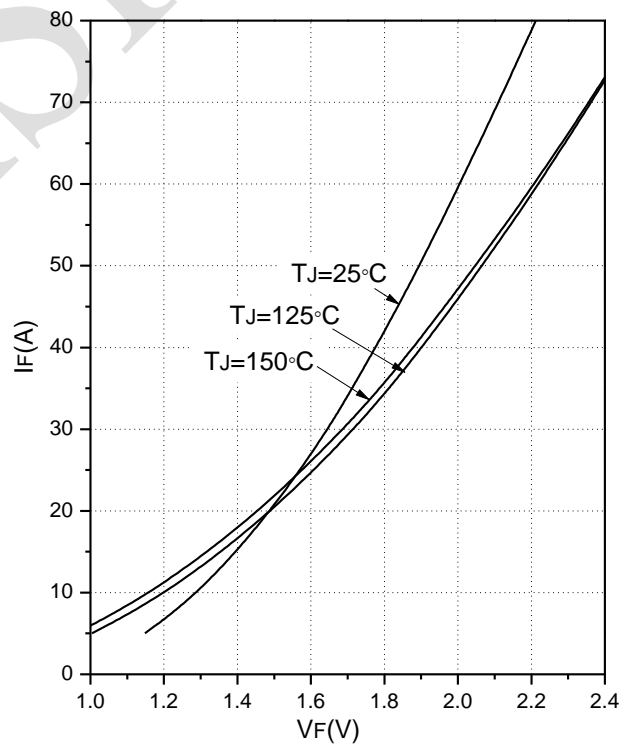


Fig.4 Forward Characteristics of FWD

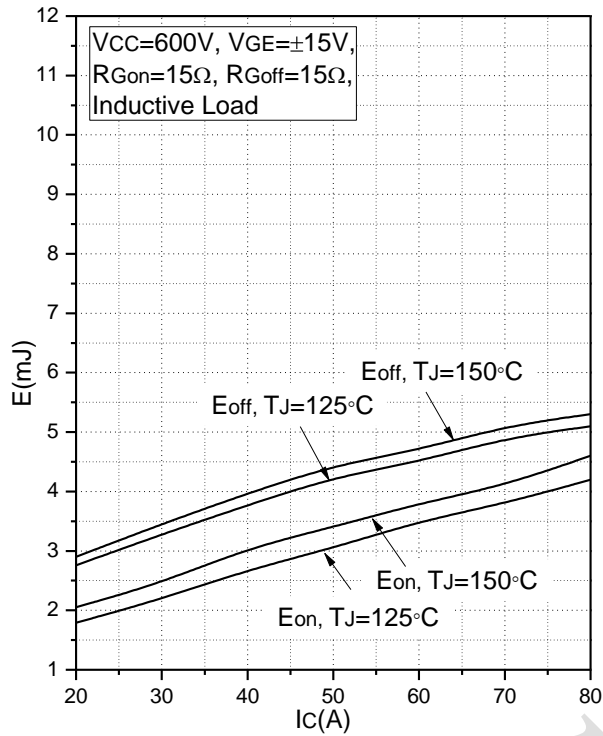


Fig.5 Typical Switching Loss vs. Collector Current

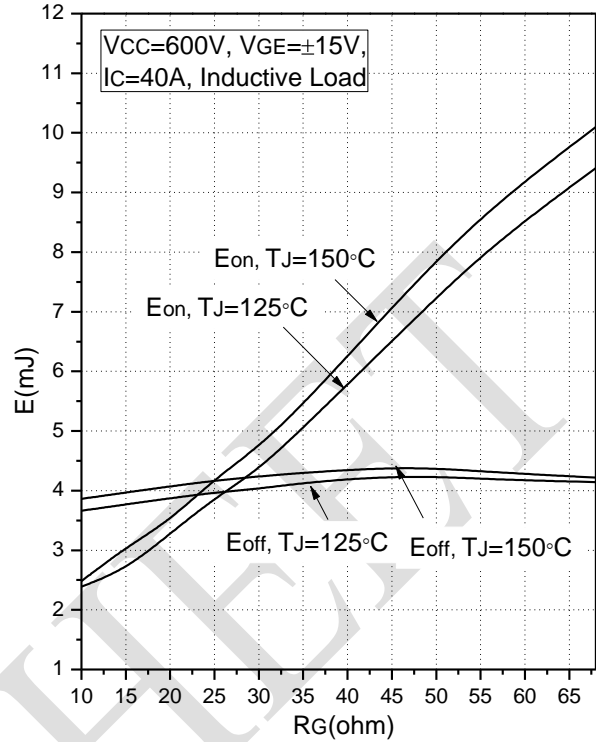


Fig.6 Typical Switching Loss vs. Gate Resistance

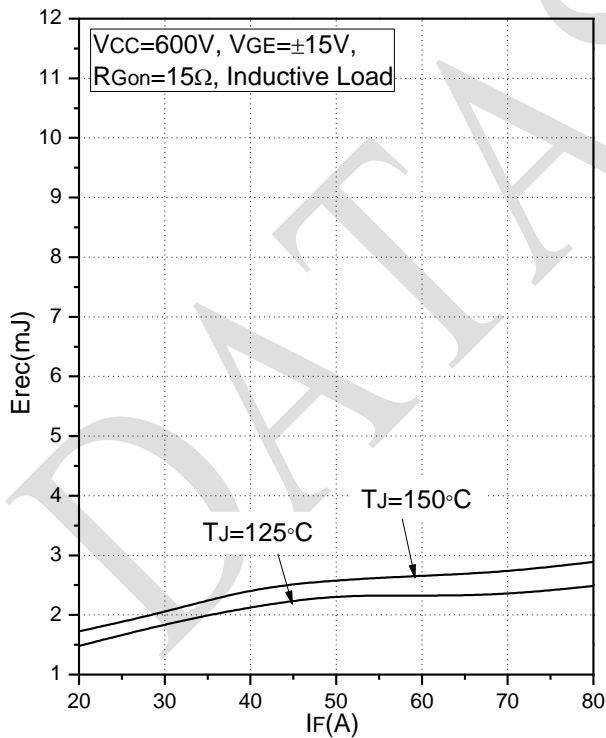


Fig.7 Typical Switching Loss vs. Forward Current

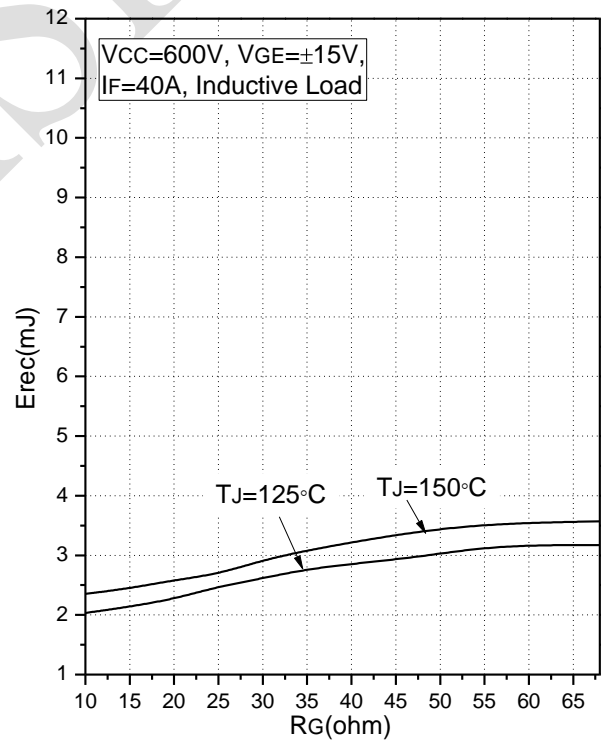


Fig.8 Typical Switching Loss vs. Gate Resistance

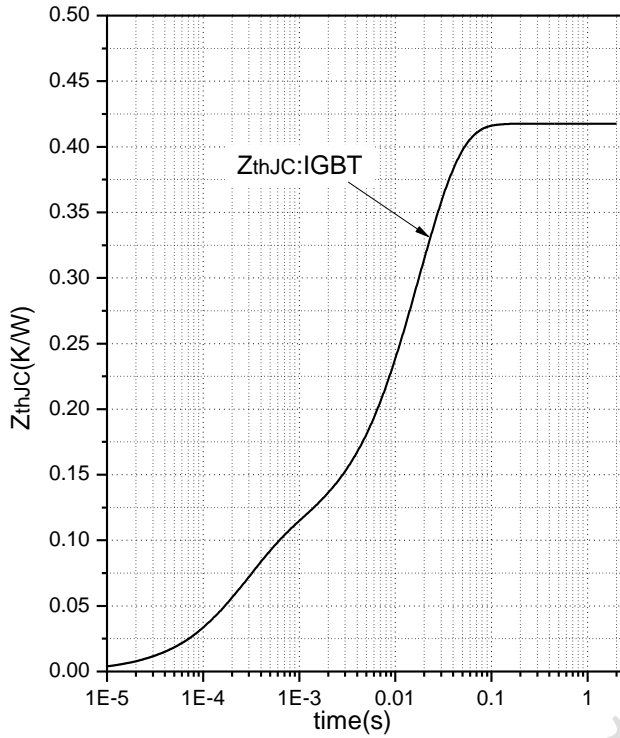


Fig.9 Transient Thermal Impedance

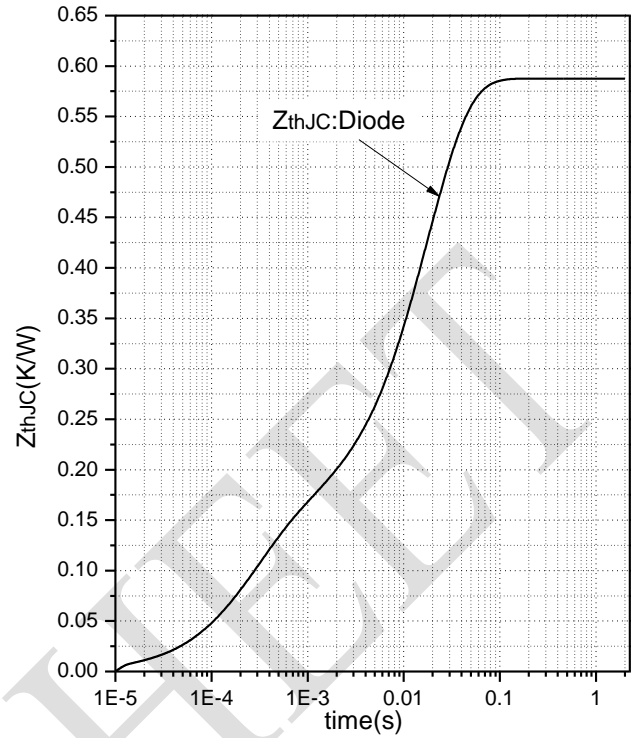


Fig.10 Transient Thermal Impedance

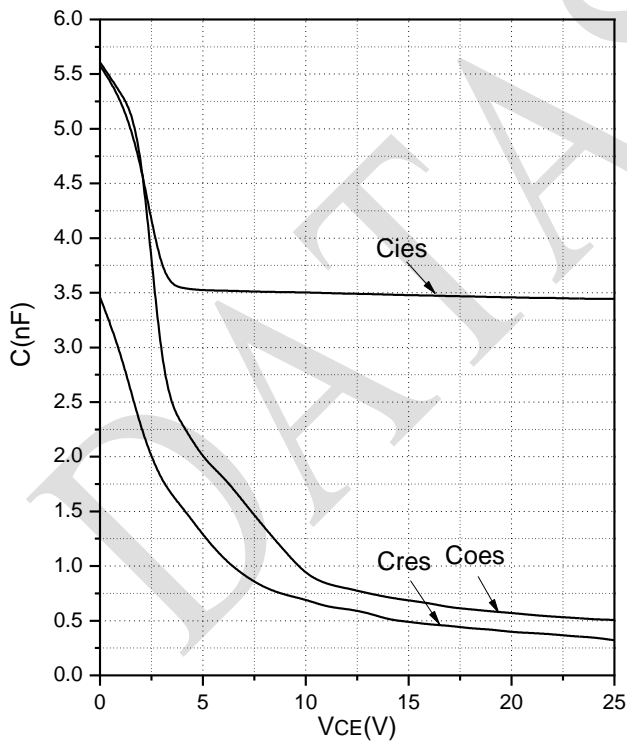


Fig.11 Capacitance Characteristics

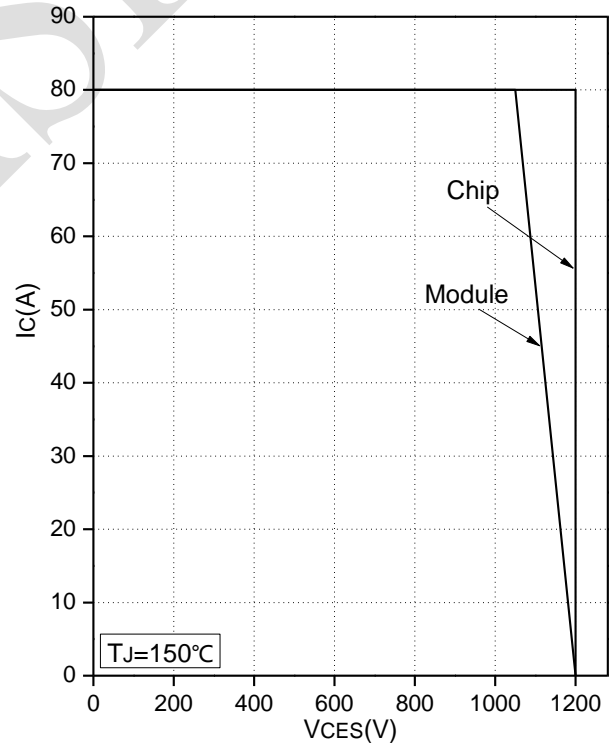


Fig.12 Reverse Bias Safe Operation Area (RBSOA)

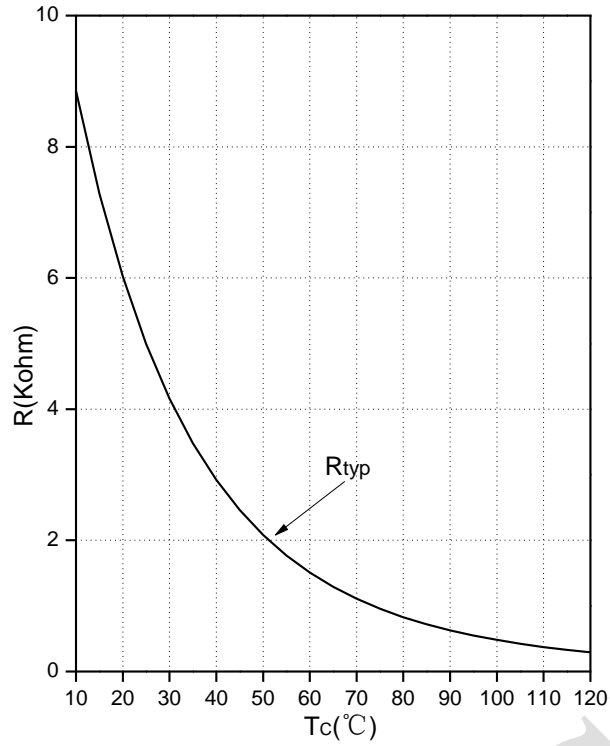
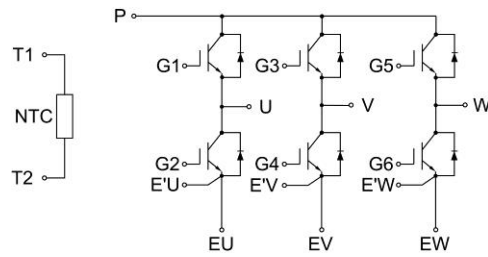


Fig.13 NTC Temperature Characteristics

DATA SHEET

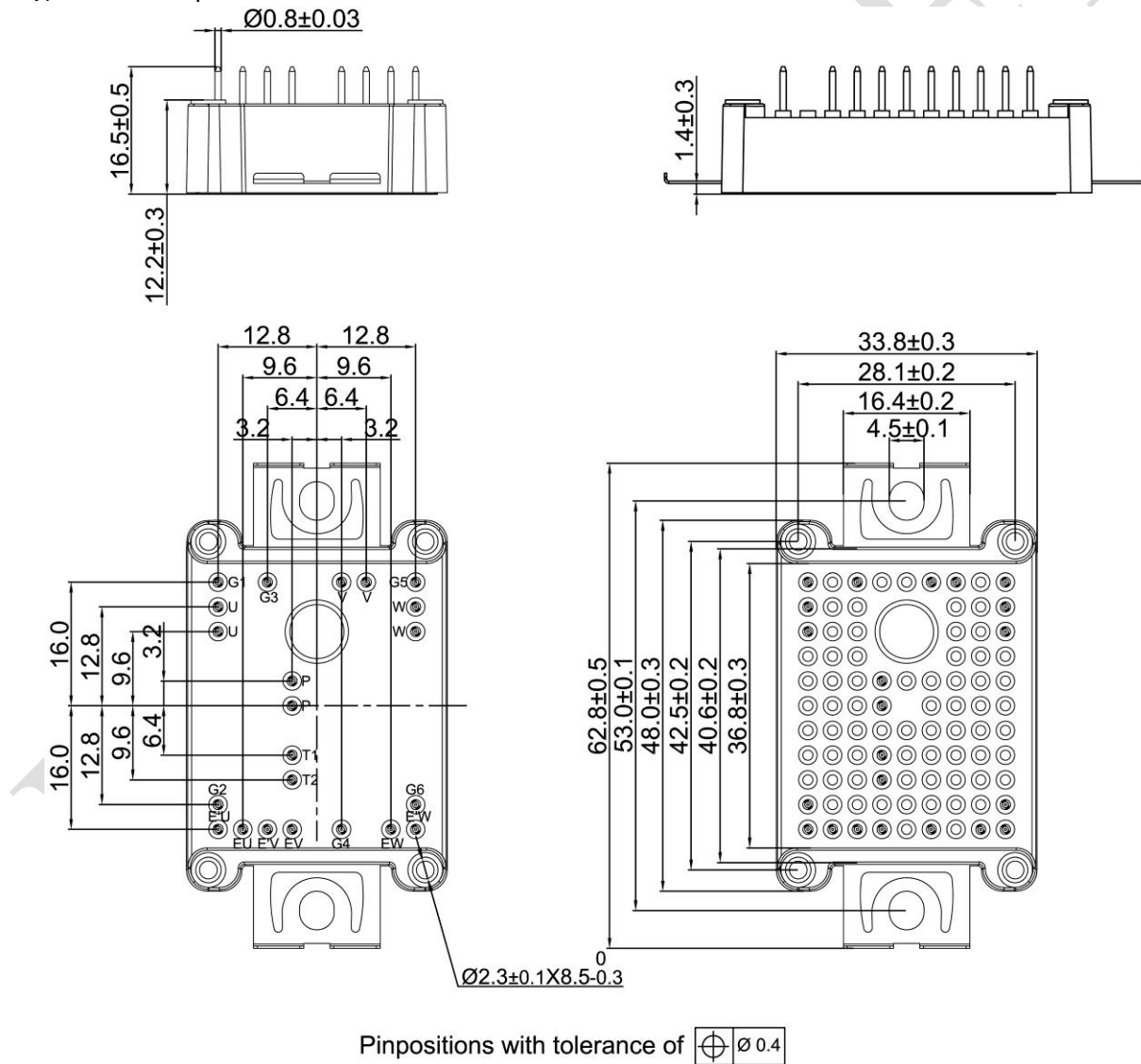


Internal Circuit:



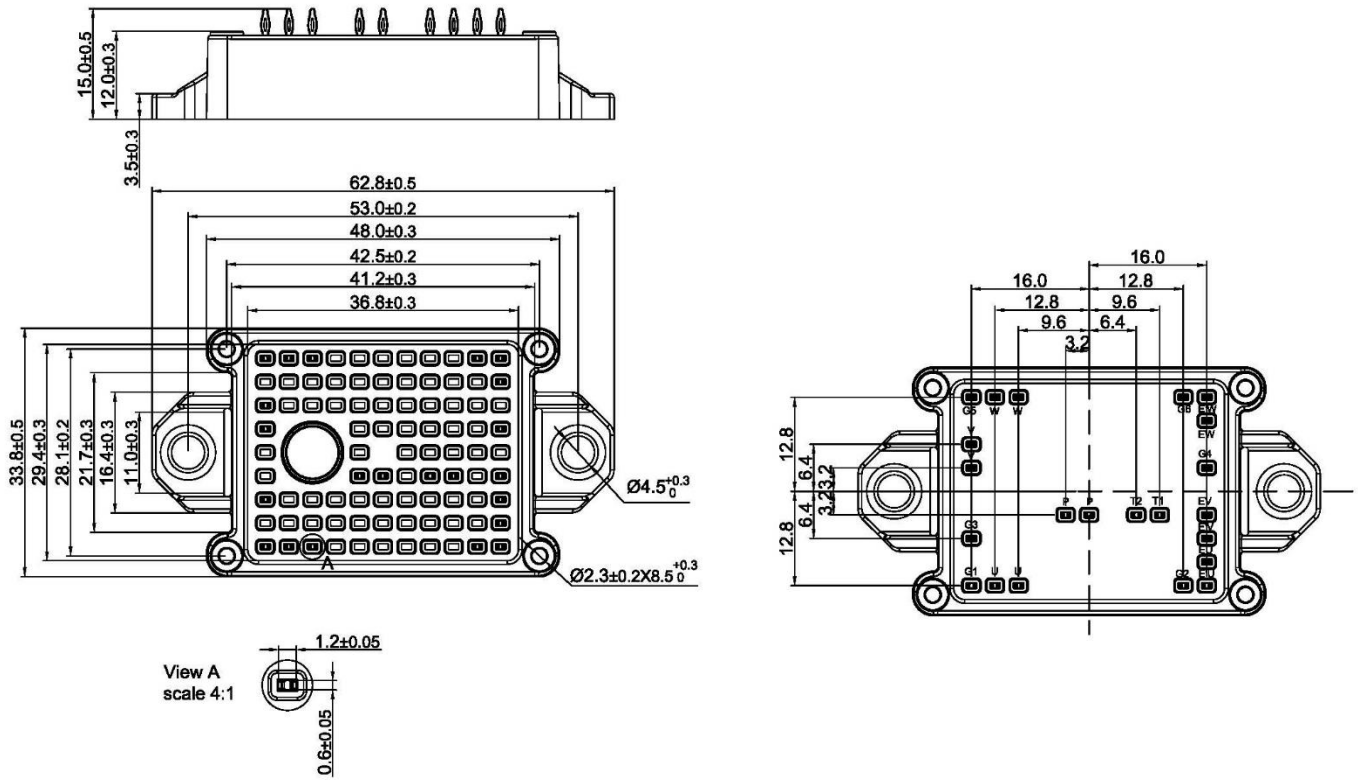
Package Outline (Unit: mm):

Pins type I --Solder pins





Pins type II--Press-fit pins





Date	Revision	Notes
05/31/2023	01	Initial Release

Announcements

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DATA SHEET